

TRANSISTOR (NPN)
Plastic-Encapsulate Transistor
FEATURES

Power dissipation

$$P_{CM}: 0.625W (T_{amb}=25^{\circ}C)$$

Collector current

$$I_{CM}: 0.2A$$

Collector-base voltage

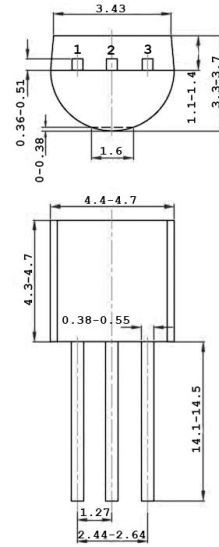
$$V_{(BR)CBO}: 40V$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^{\circ}C \text{ to } +150^{\circ}C$$

TO-92

1. EMITTER
2. COLLECTOR
3. BASE



UNIT:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100 \mu A, I_E=0$	40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	30		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100 \mu A, I_C=0$	4		V
Collector cut-off current	I_{CBO}	$V_{CB}=40V, I_E=0$		0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$		0.5	μA
DC current gain	h_{FE}	$V_{CE}=6V, I_C=1mA$	40	200	
Transition frequency	f_r	$V_{CE}=6V, I_C=1mA$	450		MHz

CLASSIFICATION OF h_{FE}

Rank	R	O	Y
Range	40-80	70-140	100-200